

# Fourfold Azimuthal Dependence of Terahertz Radiation from (100) Silicon

Quan Guo<sup>1</sup>, Lei Chen<sup>1</sup>, Dong-wen Zhang<sup>1</sup>, Xiao-wei Wang<sup>1</sup>, Zhi-hui Lv<sup>1</sup>, Chao Meng<sup>1</sup>, Yin-dong Huang<sup>1</sup>, Yi-lei Ge<sup>1</sup>, and Jian-min Yuan<sup>1</sup>

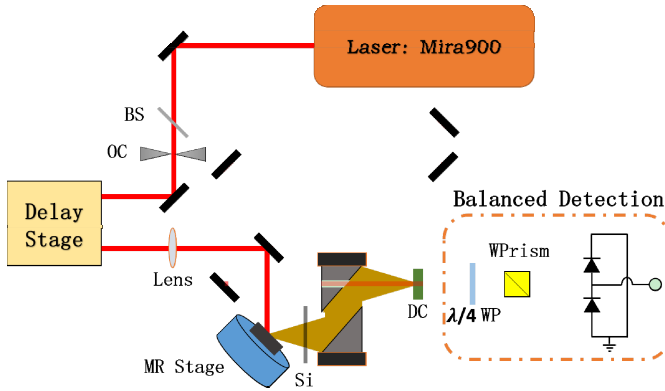
<sup>1</sup>The College of Science, National University of Defense Technology, Changsha, 410073 China

**Abstract**—A fourfold-azimuthal dependence of terahertz radiation from polished mono-crystalline (100) silicon is observed firstly. This phenomenon is explained by the electric quadrupole-magnetic dipole, which resemble second harmonic generation from (100) silicon.

## I. INTRODUCTION

AS we know, several properties are needed for efficient terahertz emission from semiconductor surfaces, such as high absorption in near infrared, high electron mobilities, fast recombination rates and short carrier lifetimes. However, mono-crystalline silicon doesn't possess these properties.[1][2] So silicon is rarely used as terahertz emitters. In order to change the properties of silicon, various methods, such as irradiation induced-defects, disorder needles perpendicular to the surface, vertically aligned silicon nanowire (Si NW) arrays, and argon implanted, is carried out on silicon surfaces.[3]-[5] Although many trials have been implemented to improve terahertz emission from silicon, there are few specific reports of terahertz emission from mono-crystalline silicon.

## II. RESULTS

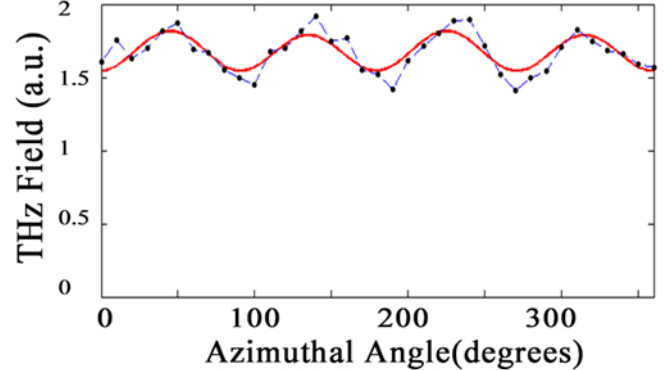


**Fig. 1.** Schematic diagram of experimental setup. BS, Beam Splitter; OC, Optical Chopper; MR Stage, Motorized Rotary Stage; Si, Silicon used to block pump light; DC, 3-mm thick ZnTe Detection Crystal; WP, Wave Plate; WPrism, Wollaston Prism.

In our work, the azimuthal dependence of terahertz radiation from (100) silicon was studied by a home-built THz-TDS. Fig. 1 shows the experimental setup.

The laser source was a Ti: Sapphire oscillator (Mira900, coherent) generating p-polarized light pulse of 150fs duration, centered at a wavelength of 800nm with a repetition rate of 78MHz. The average pump power was 1.5W, which was directed onto the sample at a 45° angle of incidence and focused to 1.5 mm diameter on the sample. In the reflecting direction, the generated terahertz from (100) silicon was collected and focused by two parabolic mirrors. Then the focused terahertz was detected by standard electro-optic

sampling techniques in a 3mm thick (110) ZnTe detection crystal.



**Fig. 2.** The azimuthal dependence of THz radiation from (100) silicon with p-type and the resistivity of 1~5 Ω·cm

A fourfold azimuthal dependence of terahertz radiation from (100) silicon surfaces is shown in Fig. 2. It is obvious that this azimuthal dependence is very similar with that of second harmonic generation (SHG), which displays the lattice symmetry of silicon. [6] As far as we know, it's the first time that the silicon symmetry was detected in this way. Comparing THz and SHG from (100) silicon, we can conclude that the azimuthal dependence we found should be attributed to the electric quadrupole-magnetic dipole (EQMD) of (100) silicon.

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